LIST OF CURRENT CLAIMS

1. (Currently Amended) A substrate voltage generating circuit, comprising:

a first power supply node supplied with a first potential level;

a second power supply node supplied with a second potential level lower than the first potential level;

an output node having a third potential level lower than the second potential level;

a level shift circuit which is coupled between the first power supply node and the output node, which receives a first input signal and a second input signal complement of the first input signal, and which outputs an output signal having the first potential level and the third potential level; and

a switch circuit which connects the second power supply node to the output node in response to the output signal;

wherein the switch circuit includes a switching element, which has a control electrode receiving the output signal, a first electrode connected to the second power supply node, and a second electrode connected to the output node; and

a capacitor coupled between the first electrode and the control electrode.

2. (Previously Presented) The substrate voltage generating circuit according to claim 1, wherein the level shift circuit comprises:

a first transistor of a first conductivity type which has a gate receiving the first input signal, a source connected to the first power supply node, and a drain;

a second transistor of the first conductivity type which has a gate receiving the second input signal complement of the first input signal, a source connected to the first power supply node, and a drain coupled to the switch circuit;

a third transistor of a second conductivity type which has a gate connected to the gate of the first transistor, a source, a drain connected to the drain of the first transistor, and a gate oxide film having a first thickness;

a fourth transistor of the second conductivity type which has a gate connected to the gate of the second transistor, a source, a drain connected to the drain of the second transistor, and a gate oxide film having the first thickness;

a fifth transistor of the second conductivity type which has a gate connected to the drain of the second transistor, a source connected to the output node, a drain connected to the source of the third transistor, and a gate oxide film having a second thickness thinner than the first thickness; and

a sixth transistor of the second conductivity type which has a gate connected to the drain of the first transistor, a source connected to the output node, a drain connected to the source of the fourth transistor, and a gate oxide film having the second thickness.

3. (Previously Presented) The substrate voltage generating circuit according to claim 1, wherein the level shift circuit comprises:

a first transistor of a first conductivity type which has a gate receiving the first input signal, a source connected to the first power supply node, and a drain;

a second transistor of the first conductivity type which has a gate receiving the second input signal complement of the first input signal, a source connected to the first power supply node, and a drain coupled to the switch circuit;

a third transistor of a second conductivity type which has a gate connected to the drain of the second transistor, a source, a drain connected to the drain of the first transistor, and a gate oxide film having a first thickness; a fourth transistor of the second conductivity type which has a gate connected to the drain of the first transistor, a source, a drain connected to the drain of the second transistor, and a gate oxide film having the first thickness;

a fifth transistor of the second conductivity type which has a gate connected to the gate of the first transistor, a source connected to the output node, a drain connected to the source of the third transistor, and a gate oxide film having a second thickness thicker than the first thickness; and

a sixth transistor of the second conductivity type which has a gate connected to the gate of the second transistor, a source connected to the output node, a drain connected to the source of the fourth transistor, and a gate oxide film having the second thickness.

4. (Cancelled)

5. (Original) The substrate voltage generating circuit according to claim 1, wherein the second potential level is 0 volt.

6. (Original) The substrate voltage generating circuit according to claim 1, wherein the third potential level is a negative voltage level.

7. – 10. (Cancelled)